

SCHOTTKY BARRIER DIODE

Features

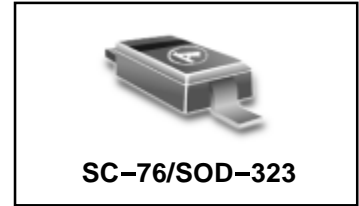
- (1) Small surface mounting type SC-76/SOD-323
- (2) Low reverse current and low forward voltage.
- (3) High reliability

Construction

silicon epitaxial planar

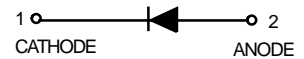
We declare that the material of product compliance with RoHS requirements.

LRB751V-40T1G



ORDERING INFORMATION

Device	Package	Shipping
LRB751V-40T1G	SOD-323/SC-76	3000/Tape&Reel
LRB751V-40T3G	SOD-323/SC-76	10000/Tape&Reel



MAXIMUM RATINGS (T_A = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	V _R	30	V
Mean rectifying current	I _O	30	mA
Peak forward surge current*	I _{FSM}	200	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40~+125	°C

*60Hz for 1

DEVICE MARKING

LRB751V-40T1G= 5E

ELECTRICAL CHARACTERISTICS(T_A = 25°C)

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Forward voltage	V _F	-	-	0.37	V	I _F =1mA
Reverse current	I _R	-	-	0.5	μA	V _R =30V
Capacitance between terminals	C _T	-	2.0	-	pF	V _R =1V, f=1MHz

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Electrical characteristic curves($T_A = 25^\circ\text{C}$)

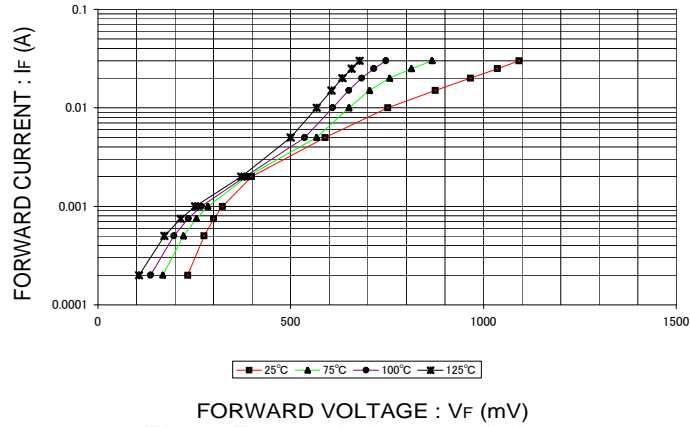


Fig. 1 Forward characteristics

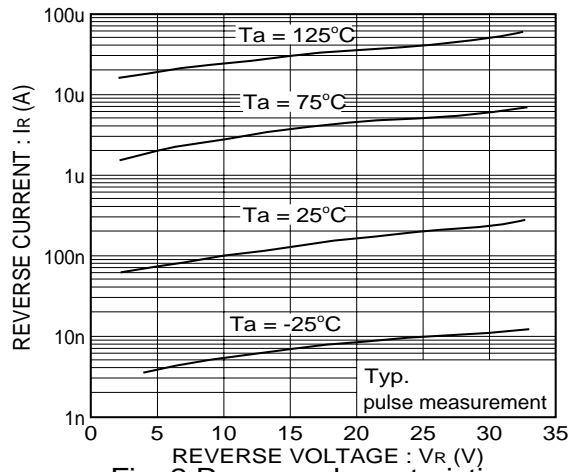


Fig. 2 Reverse characteristics

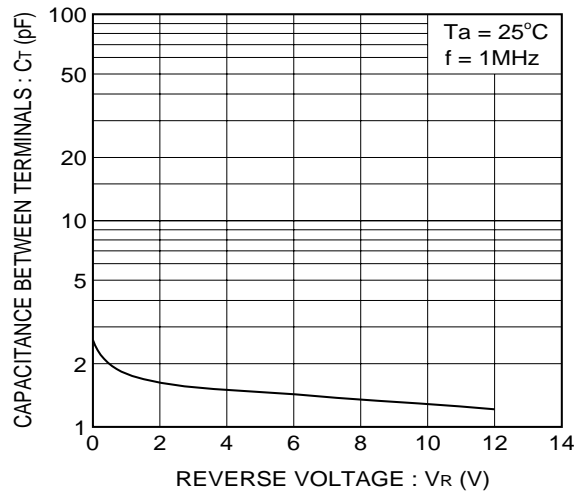
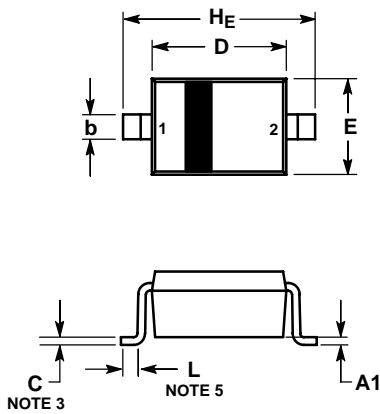


Fig. 3 Capacitance between terminals characteristics

LRB751V- 40T1G
SOD-323

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURED FROM END OF RADIUS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
H_E	2.30	2.50	2.70	0.090	0.098	0.105

SOLDERING FOOTPRINT*
